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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII)

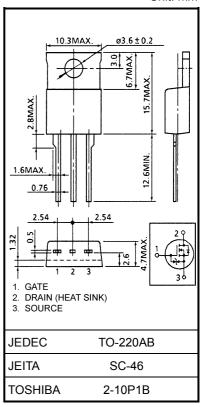
2SK2603

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $R_{DS}(ON) = 3.0 \Omega$ (typ.)
- High forward transfer admittance $|Y_{fs}| = 2.6 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 640 \ V)$
- Enhancement-mode : $V_{th} = 2.0 \sim 4.0 V (V_{DS} = 10 V, I_D = 1 mA)$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	800	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	800	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	3	А	
	Pulse (Note 1)	I _{DP}	9	A	
Drain power dissipation	n (Tc = 25°C)	PD	100	W	
Single pulse avalanche energy (Note 2)		E _{AS}	300	mJ	
Avalanche current		I _{AR}	3	А	
Repetitive avalanche energy (Note 3)		E _{AR}	10.0	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 2.0 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	1.25	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	83.3	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 60.0 mH, I_{AR} = 6 A, R_G = 25 Ω

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution. Unit: mm

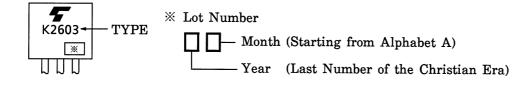
Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	irrent	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V	_		±10	μA
Gate-source bre	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 640 V, V _{GS} = 0 V	_	-	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	800	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 1.5 A,		3.0	3.6	Ω
Forward transfe	admittance	Y _{fs}	V _{DS} = 20 V, I _D = 1.5 A	0.65	2.6	_	S
Input capacitance	e	C _{iss}			750	_	
Reverse transfe	r capacitance	C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		10	_	pF
Output capacitance		Coss		_	70		1
Switching time	Rise time	tr	$V_{GS} \stackrel{10 \text{ V}}{}_{0 \text{ V}} \prod_{O \\ U \\ $	_	15	_	
	Turn-on time	t _{on}		_	55	_	20
	Fall time	t _f		_	30	_	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w = 10 µs	_	110	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	25	—	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 3 A		13	—	nC
Gate-drain ("miller") Charge		Q _{gd}			12	_	

Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	3	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	9	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 3 A, V _{GS} = 0 V	_	_	-1.9	V
Reverse recovery time	t _{rr}	I _{DR} = 3 A, V _{GS} = 0 V, dI _{DR} / dt = 100 A / μs	—	900		ns
Reverse recovery charge	Q _{rr}			6	_	μC

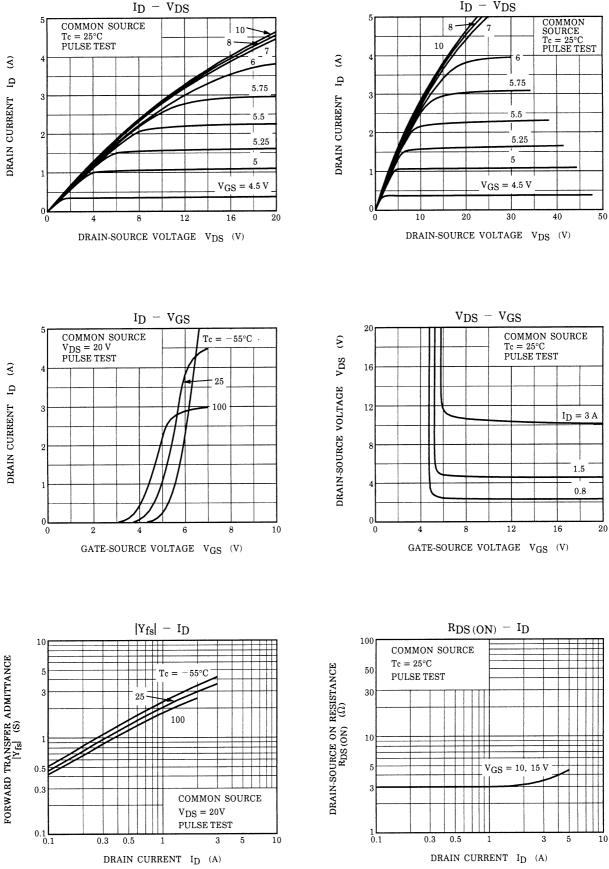
Marking



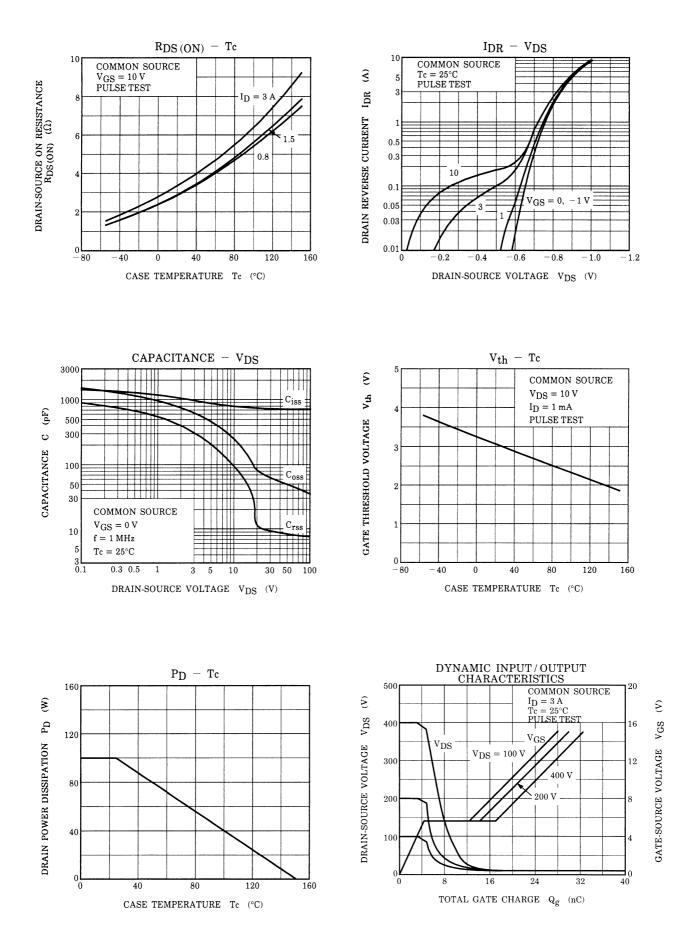
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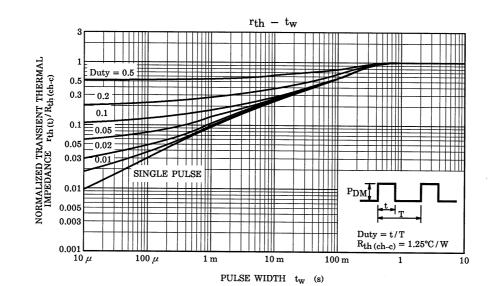
 $I_D - V_{DS}$

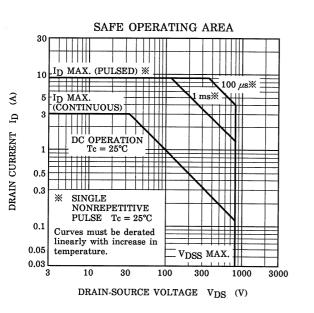
Ś ŋ DRAIN CURRENT

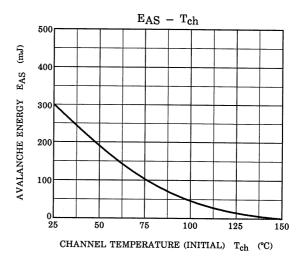


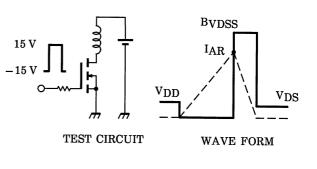
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$$\begin{array}{l} \mathrm{RG} = 25 \ \Omega \\ \mathrm{VDD} = 90 \ \mathrm{V}, \ \mathrm{L} = 60 \ \mathrm{mH} \end{array} \qquad \mathrm{E_{AS}} = \frac{1}{2} \cdot \mathrm{L} \cdot \mathrm{I}^2 \cdot \left(\frac{\mathrm{B} \mathrm{VDSS}}{\mathrm{B} \mathrm{VDSS} - \mathrm{VDD}} \right) \end{array}$$

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